

**Amendments to the Abstract:**

Please amend the Abstract as follows:

Thin-layer electronic device, in particular a thin-layer power device, and process for fabricating this device. According to the invention, an electronic device is formed comprising an active part ~~(38,40,42)~~, a first thin layer ~~[(36)]~~ which is made of a semiconductor material and in which this active part is formed, and a substrate ~~[(44)]~~ which is made of a conductive material. This device also comprises a carrier recombination zone ~~[(46)]~~ which is located between the substrate and the first thin layer and which also ensures a resistive electric contact between this substrate and this first thin layer.